

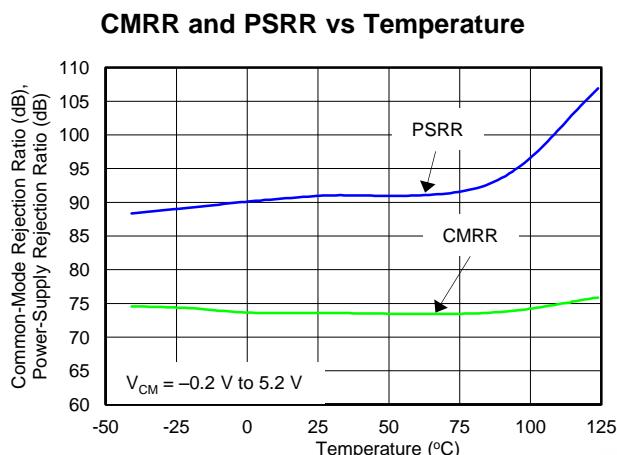
# TLV600x Low-Power, Rail-to-Rail In/Out, 1-MHz Operational Amplifier for Cost-Sensitive Systems

## 1 Features

- Precision Amplifiers for Cost-Sensitive Systems
- Low Quiescent Current: 75  $\mu$ A/ch
- Supply Range: 1.8 V to 5.5 V
- Input Voltage Noise Density: 28 nV/ $\sqrt{\text{Hz}}$  at 1 kHz
- Rail-to-Rail Input and Output
- Gain Bandwidth: 1 MHz
- Low Input Bias Current: 1 pA
- Low Offset Voltage: 0.75 mV
- Unity-Gain Stable
- Internal RF and EMI Filter
- Extended Temperature Range:  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

## 2 Applications

- Industrial and Consumer Electronics
- Portable Equipment
- Portable Blood Glucose Systems
- Smoke Detectors
- White Goods
- Power Banks



## 3 Description

The TLV600x family of single-, dual-, and quad-channel operational amplifiers is specifically designed for general-purpose applications. Featuring rail-to-rail input and output (RRIO) swings, low quiescent current (75  $\mu$ A, typical), wide bandwidth (1 MHz) and low noise (28 nV/ $\sqrt{\text{Hz}}$  at 1 kHz), this family is attractive for a variety of applications that require a good balance between cost and performance, such as consumer electronics, smoke detectors, and white goods. The low-input-bias current ( $\pm 1.0$  pA, typical) enables the TLV600x to be used in applications with megohm source impedances.

The robust design of the TLV600x provides ease-of-use to the circuit designer: unity-gain stability with capacitive loads of up to 150 pF, integrated RF/EMI rejection filter, no phase reversal in overdrive conditions, and high electrostatic discharge (ESD) protection (4-kV HBM).

The devices are optimized for operation at voltages as low as 1.8 V ( $\pm 0.9$  V) and up to 5.5 V ( $\pm 2.75$  V), and are specified over the extended temperature range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ .

The single-channel TLV6001 is available in SC70-5 and SOT23-5 packages. The dual-channel TLV6002 is offered in SOIC-8 and VSSOP-8 packages, and the quad-channel TLV6004 is offered in a TSSOP-14 package.

## Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TLV6001	SC70 (5)	2.00 mm x 1.25 mm
	SOT-23 (5)	2.90 mm x 1.60 mm
TLV6002	SOIC (8)	4.90 mm x 3.91 mm
	VSSOP (8)	3.00 mm x 3.00 mm
TLV6004	TSSOP (14)	5.00 mm x 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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## 4 Revision History

### Changes from Revision C (December 2016) to Revision D

		Page
•	Changed inverting input pin to noninverting input pin in <i>Pin Functions</i> : <i>TLV6001</i> table .....	3
•	Changed inverting input pin to noninverting input pin in <i>Pin Functions</i> : <i>TLV6001R</i> table .....	4
•	Changed inverting input pin to noninverting input pin in <i>Pin Functions</i> : <i>TLV6001U</i> table .....	4
•	Changed "Sample and Buy" to "Order Now" in <i>Related Links</i> table .....	21

### Changes from Revision B (October 2016) to Revision C

		Page
•	Changed all pin outs in <i>Pin Configuration and Functions</i> section to reflect correct pin names and order.....	3

### Changes from Revision A (July 2016) to Revision B

		Page
•	Added <i>TLV6001R</i> pinout drawing to <i>Pin Configurations and Functions</i> section .....	4
•	Added <i>TLV6001U</i> pinout drawing to <i>Pin Configurations and Functions</i> section .....	4

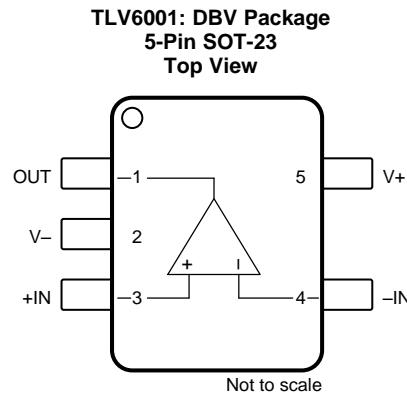
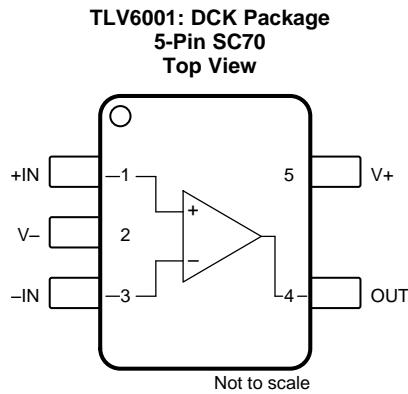
### Changes from Original (June 2016) to Revision A

		Page
•	Changed Product Status from Product Preview to Production Data .....	1
•	Changed formatting of the <i>Related Documentation</i> section. .....	21
•	Changed wording of the <i>Receiving Notification of Documentation Updates</i> section .....	21

## 5 Device Comparison Table

DEVICE	NO. OF CHANNELS	PACKAGE-LEADS				
		SC70	SOT-23	SOIC	VSSOP	TSSOP
TLV6001	1	5	5	—	—	—
TLV6002	2	—	—	8	8	—
TLV6004	4	—	—	—	—	14

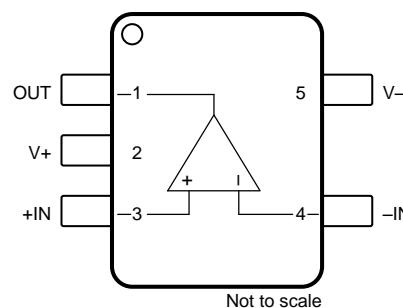
## 6 Pin Configuration and Functions



### Pin Functions: TLV6001

PIN			I/O	DESCRIPTION
NAME	DCK (SC70)	DBV (SOT-23)		
-IN	3	4	I	Inverting input
+IN	1	3	I	Noninverting input
OUT	4	1	O	Output
V-	2	2	—	Negative (lowest) power supply
V+	5	5	—	Positive (highest) power supply

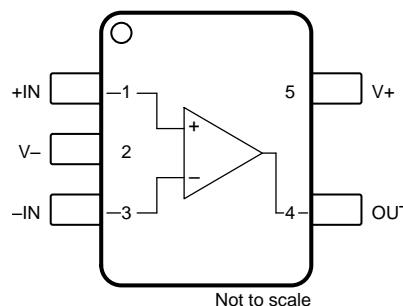
**TLV6001R: DBV Package  
5-Pin SOT-23  
Top View**



**Pin Functions: TLV6001R**

PIN		I/O	DESCRIPTION
NAME	NO.		
-IN	4	I	Inverting input
+IN	3	I	Noninverting input
OUT	1	O	Output
V-	5	—	Negative (lowest) power supply
V+	2	—	Positive (highest) power supply

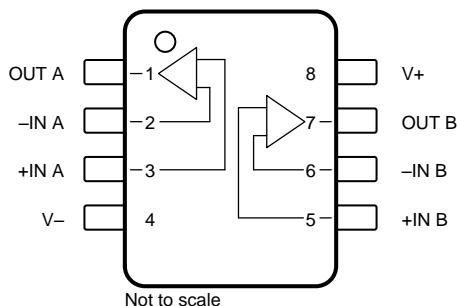
**TLV6001U: DBV Package  
5-Pin SOT-23  
Top View**



**Pin Functions: TLV6001U**

PIN		I/O	DESCRIPTION
NAME	NO.		
-IN	3	I	Inverting input
+IN	1	I	Noninverting input
OUT	4	O	Output
V-	2	—	Negative (lowest) power supply
V+	5	—	Positive (highest) power supply

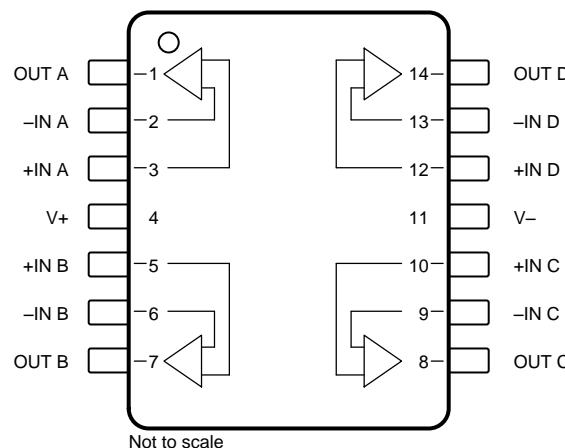
**TLV6002: D, DGK Packages**  
**8-Pin SOIC, 8-Pin VSSOP**  
**TLV6002 Top View**



**Pin Functions: TLV6002**

PIN			I/O	DESCRIPTION
NAME	D (SOIC)	DGK (VSSOP)		
-IN A	2	2	I	Inverting input, channel A
-IN B	6	6	I	Inverting input, channel B
+IN A	3	3	I	Noninverting input, channel A
+IN B	5	5	I	Noninverting input, channel B
OUT A	1	1	O	Output, channel A
OUT B	7	7	O	Output, channel B
V-	4	4	—	Negative (lowest) power supply
V+	8	8	—	Positive (highest) power supply

**TLV6004: PW Package  
14-Pin TSSOP  
Top View**



**Pin Functions: TLV6004**

PIN		I/O	DESCRIPTION
NAME	NO.		
-IN A	2	I	Inverting input, channel A
-IN B	6	I	Inverting input, channel B
-IN C	9	I	Inverting input, channel C
-IN D	13	I	Inverting input, channel D
+IN A	3	I	Noninverting input, channel A
+IN B	5	I	Noninverting input, channel B
+IN C	10	I	Noninverting input, channel C
+IN D	12	I	Noninverting input, channel D
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
OUT C	8	O	Output, channel C
OUT D	14	O	Output, channel D
V-	11	—	Negative (lowest) power supply
V+	4	—	Positive (highest) power supply

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	Supply voltage		7	V
	Signal input pins, voltage <sup>(2)</sup>	(V-) – 0.5	(V+) + 0.5	V
Current	Signal input pins, current <sup>(2)</sup>	-10	10	mA
	Output short-circuit <sup>(3)</sup>	Continuous		mA
Temperature	Operating, $T_A$	-40	150	°C
	Junction, $T_J$		150	°C
	Storage, $T_{stg}$	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.

### 7.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	$\pm 4000$
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	$\pm 1000$

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_S$	Supply voltage	1.8	5.5	V
$T_A$	Specified temperature range	-40	125	°C

## 7.4 Thermal Information: TLV6001

THERMAL METRIC <sup>(1)</sup>	TLV6001		UNIT
	DBV (SOT-23)	DCK (SC70)	
	5 PINS	5 PINS	
R <sub>θJA</sub> Junction-to-ambient thermal resistance	228.5	281.4	°C/W
R <sub>θJC(top)</sub> Junction-to-case (top) thermal resistance	99.1	91.6	°C/W
R <sub>θJB</sub> Junction-to-board thermal resistance	54.6	59.6	°C/W
Ψ <sub>JT</sub> Junction-to-top characterization parameter	7.7	1.5	°C/W
Ψ <sub>JB</sub> Junction-to-board characterization parameter	53.8	58.8	°C/W
R <sub>θJC(bot)</sub> Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 7.5 Thermal Information: TLV6002

THERMAL METRIC <sup>(1)</sup>	TLV6002		UNIT
	D (SOIC)	DGK (VSSOP)	
	8 PINS	8 PINS	
R <sub>θJA</sub> Junction-to-ambient thermal resistance	138.4	191.2	°C/W
R <sub>θJC(top)</sub> Junction-to-case (top) thermal resistance	89.5	61.9	°C/W
R <sub>θJB</sub> Junction-to-board thermal resistance	78.6	111.9	°C/W
Ψ <sub>JT</sub> Junction-to-top characterization parameter	29.9	5.1	°C/W
Ψ <sub>JB</sub> Junction-to-board characterization parameter	78.1	110.2	°C/W
R <sub>θJC(bot)</sub> Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 7.6 Thermal Information: TLV6004

THERMAL METRIC <sup>(1)</sup>	TLV6004		UNIT
	PW (TSSOP)	14 PINS	
	14 PINS	14 PINS	
R <sub>θJA</sub> Junction-to-ambient thermal resistance	121.0	121.0	°C/W
R <sub>θJC(top)</sub> Junction-to-case (top) thermal resistance	49.4	49.4	°C/W
R <sub>θJB</sub> Junction-to-board thermal resistance	62.8	62.8	°C/W
Ψ <sub>JT</sub> Junction-to-top characterization parameter	5.9	5.9	°C/W
Ψ <sub>JB</sub> Junction-to-board characterization parameter	62.2	62.2	°C/W
R <sub>θJC(bot)</sub> Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 7.7 Electrical Characteristics: $V_S = 1.8 \text{ V to } 5 \text{ V}$ ( $\pm 0.9 \text{ V to } \pm 2.75 \text{ V}$ )<sup>(1)</sup>

at  $T_A = 25^\circ\text{C}$ ,  $R_L = 10 \text{ k}\Omega$  connected to  $V_S / 2$ , and  $V_{CM} = V_{OUT} = V_S / 2$ , unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFFSET VOLTAGE</b>					
$V_{OS}$	Input offset voltage		0.75	4.5	mV
$dV_{OS}/dT$	$V_{OS}$ vs temperature	$T_A = -40^\circ\text{C to } 125^\circ\text{C}$		2	$\mu\text{V/}^\circ\text{C}$
PSRR	Power-supply rejection ratio		86		dB
<b>INPUT BIAS CURRENT</b>					
$I_B$	Input bias current	$T_A = 25^\circ\text{C}$	$\pm 1.0$		pA
$I_{OS}$	Input offset current		$\pm 1.0$		pA
<b>INPUT IMPEDANCE</b>					
$Z_{ID}$	Differential		100    1		$\text{M}\Omega \parallel \text{pF}$
$Z_{IC}$	Common-mode		1    5		$10^{13}\Omega \parallel \text{pF}$
<b>INPUT VOLTAGE RANGE</b>					
$V_{CM}$	Common-mode voltage range	No phase reversal, rail-to-rail input	$(V-) - 0.2$	$(V+) + 0.2$	V
CMRR	Common-mode rejection ratio	$V_{CM} = -0.2 \text{ V to } 5.7 \text{ V}$	60	76	dB
<b>OPEN-LOOP GAIN</b>					
$A_{OL}$	Open-loop voltage gain	$0.3 \text{ V} < V_O < (V+) - 0.3 \text{ V}$ , $R_L = 2 \text{ k}\Omega$	90	110	
Phase margin	$V_S = 5.0 \text{ V}$ , $G = +1$		65		degrees
<b>OUTPUT</b>					
$V_O$	Voltage output swing from supply rails	$R_L = 100 \text{ k}\Omega$	5		mV
		$R_L = 2 \text{ k}\Omega$	75	100	mV
$I_{SC}$	Short-circuit current		$\pm 15$		mA
$R_O$	Open-loop output impedance		2300		$\Omega$
<b>FREQUENCY RESPONSE</b>					
GBW	Gain-bandwidth product		1		MHz
SR	Slew rate		0.5		$\text{V}/\mu\text{s}$
$t_S$	Settling time	To 0.1%, $V_S = 5.0 \text{ V}$ , 2-V step, $G = +1$	5		$\mu\text{s}$
<b>NOISE</b>					
Input voltage noise (peak-to-peak)	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		6		$\mu\text{V}_{PP}$
$e_n$	Input voltage noise density	$f = 1 \text{ kHz}$	28		$\text{nV}/\sqrt{\text{Hz}}$
$i_n$	Input current noise density	$f = 1 \text{ kHz}$	5		$\text{fA}/\sqrt{\text{Hz}}$
<b>POWER SUPPLY</b>					
$V_S$	Specified voltage range		1.8 ( $\pm 0.9$ )	5.5 ( $\pm 2.75$ )	V
$I_Q$	Quiescent current per amplifier	$I_Q = 0 \text{ mA}$ , $V_S = 5.0 \text{ V}$		75	100 $\mu\text{A}$
Power-on time	$V_S = 0 \text{ V to } 5 \text{ V}$ , to 90% $I_Q$ level		10		$\mu\text{s}$

(1) Parameters with minimum or maximum specification limits are 100% production tested at  $25^\circ\text{C}$ , unless otherwise noted. Over-temperature limits are based on characterization and statistical analysis.

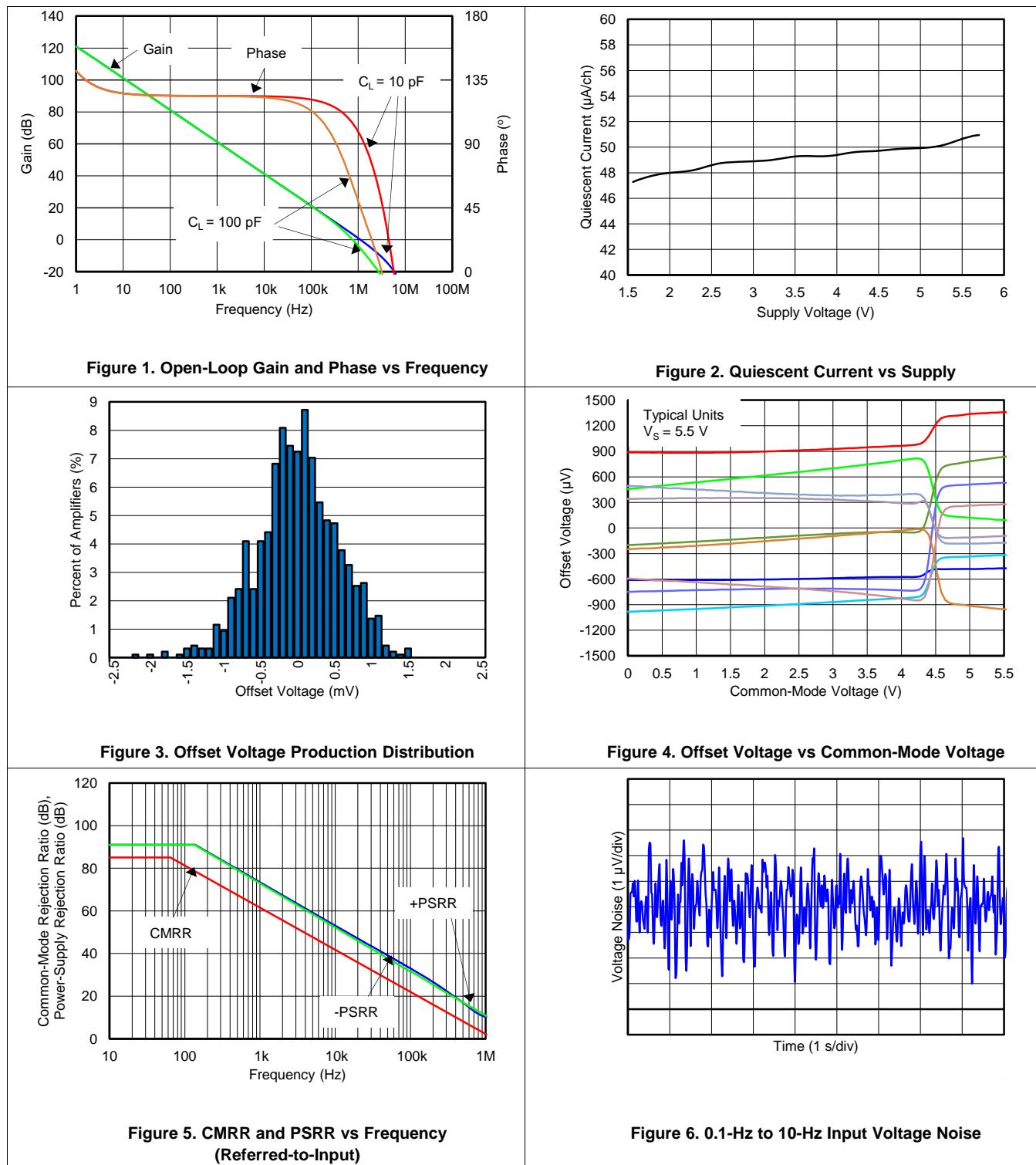
## 7.8 Typical Characteristics: Table of Graphs

**Table 1. Table of Graphs**

TITLE	FIGURE
Open-Loop Gain and Phase vs Frequency	<a href="#">Figure 1</a>
Quiescent Current vs Supply Voltage	<a href="#">Figure 2</a>
Offset Voltage Production Distribution	<a href="#">Figure 3</a>
Offset Voltage vs Common-Mode Voltage (Maximum Supply)	<a href="#">Figure 4</a>
CMRR and PSRR vs Frequency (RTI)	<a href="#">Figure 5</a>
0.1-Hz to 10-Hz Input Voltage Noise (5.5 V)	<a href="#">Figure 6</a>
Input Voltage Noise Spectral Density vs Frequency (1.8 V, 5.5 V)	<a href="#">Figure 7</a>
Input Bias and Offset Current vs Temperature	<a href="#">Figure 8</a>
Open-Loop Output Impedance vs Frequency	<a href="#">Figure 9</a>
Maximum Output Voltage vs Frequency and Supply Voltage	<a href="#">Figure 10</a>
Output Voltage Swing vs Output Current (over Temperature)	<a href="#">Figure 11</a>
Closed-Loop Gain vs Frequency, $G = 1, -1, 10$ (1.8 V)	<a href="#">Figure 12</a>
Small-Signal Step Response, Noninverting (1.8 V)	<a href="#">Figure 13</a>
Small-Signal Step Response, Noninverting (5.5 V)	<a href="#">Figure 14</a>
Large-Signal Step Response, Noninverting (1.8 V)	<a href="#">Figure 15</a>
Large-Signal Step Response, Noninverting (5.5 V)	<a href="#">Figure 16</a>
No Phase Reversal	<a href="#">Figure 17</a>
EMIRR IN+ vs Frequency	<a href="#">Figure 18</a>

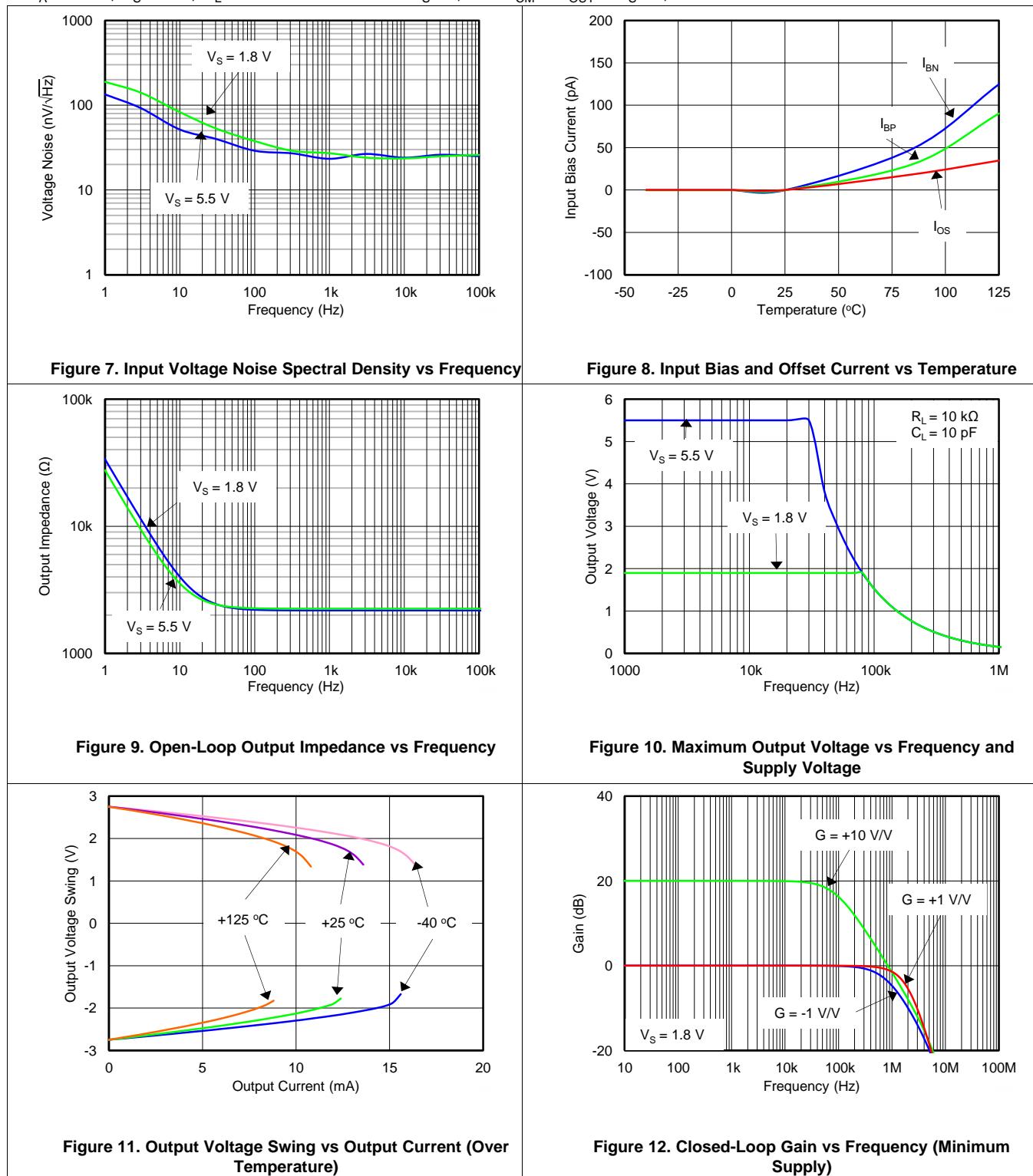
## 7.9 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ , and  $V_{CM} = V_{OUT} = V_S / 2$ , unless otherwise noted.



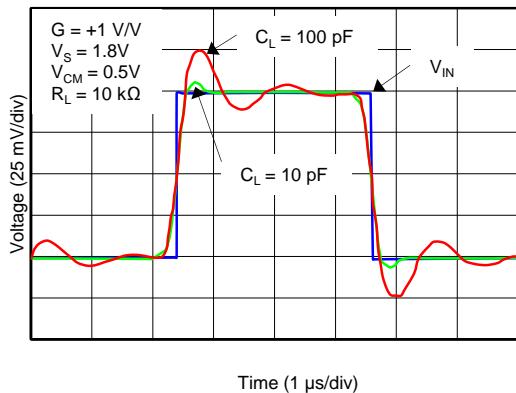
## Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ , and  $V_{CM} = V_{OUT} = V_S / 2$ , unless otherwise noted.

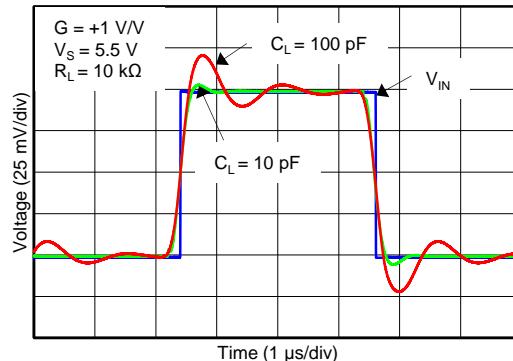


## Typical Characteristics (continued)

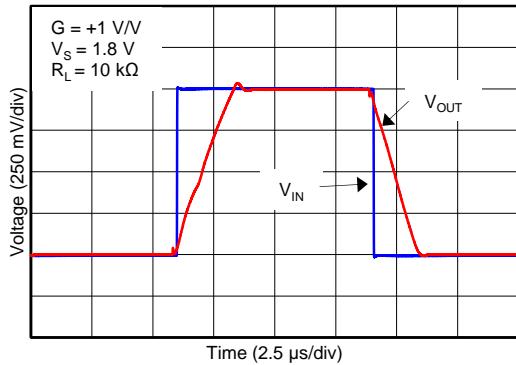
at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ , and  $V_{CM} = V_{OUT} = V_S / 2$ , unless otherwise noted.



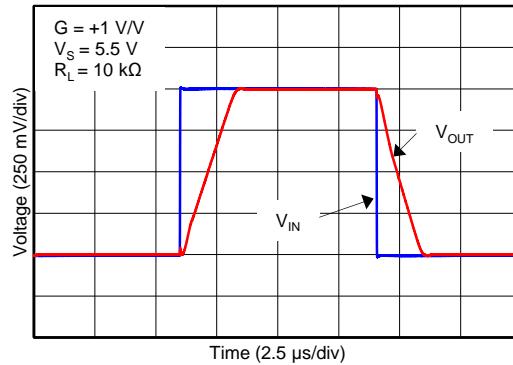
**Figure 13. Small-Signal Pulse Response  
(Minimum Supply)**



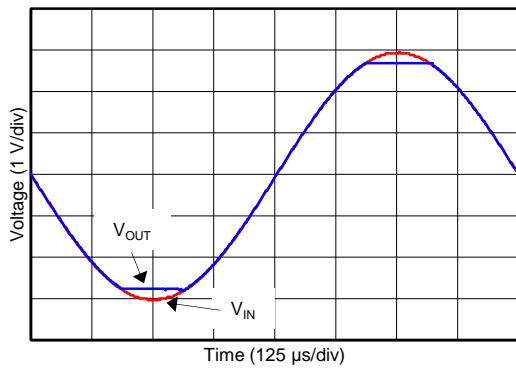
**Figure 14. Small-Signal Pulse Response  
(Maximum Supply)**



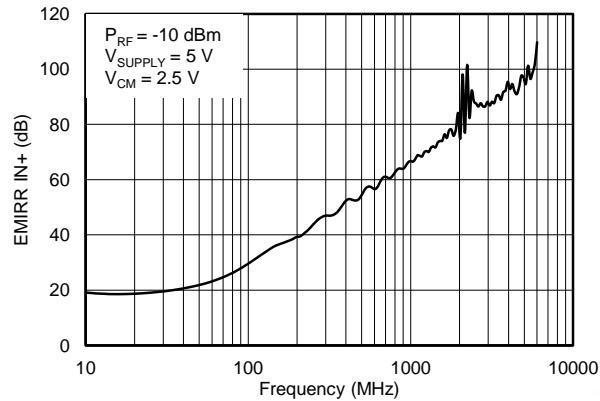
**Figure 15. Large-Signal Pulse Response  
(Minimum Supply)**



**Figure 16. Large-Signal Pulse Response  
(Maximum Supply)**



**Figure 17. No Phase Reversal**



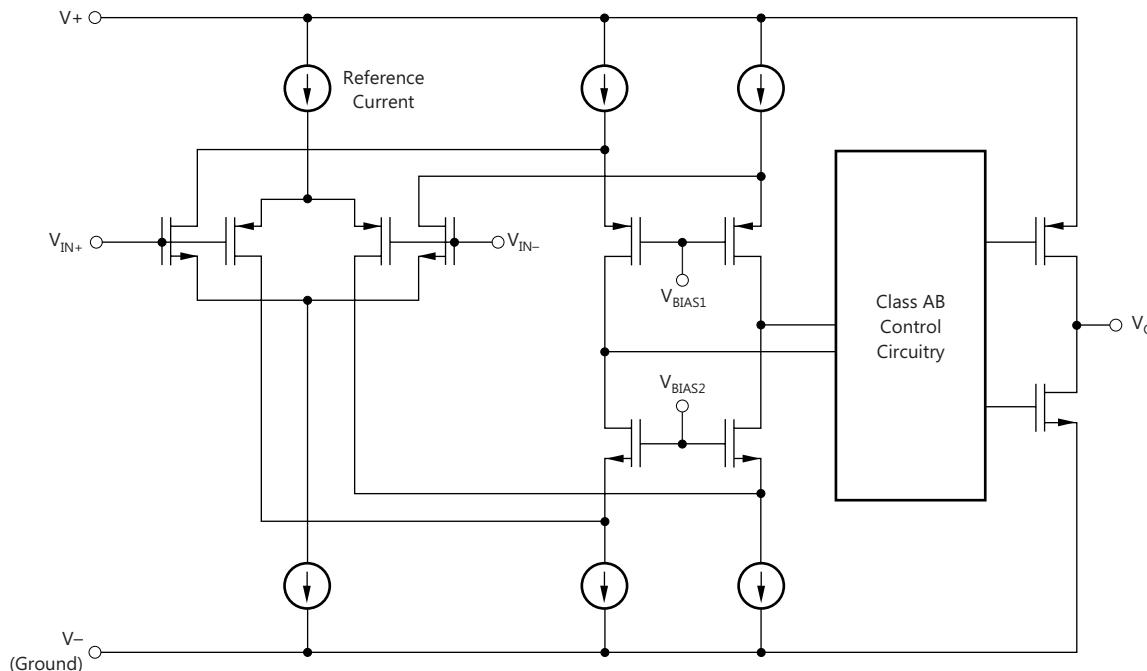
**Figure 18. EMIRR IN+ vs Frequency**

## 8 Detailed Description

### 8.1 Overview

The TLV600x family of operational amplifiers are general-purpose, low-cost devices that are suitable for a wide range of portable applications. Rail-to-rail input and output swings, low quiescent current, and wide dynamic range make the op amps well-suited for driving sampling analog-to-digital converters (ADCs) and other single-supply applications.

### 8.2 Functional Block Diagram



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## 8.3 Feature Description

### 8.3.1 Operating Voltage

The TLV600x series is fully specified and tested from 1.8 V to 5.5 V ( $\pm 0.9$  V to  $\pm 2.75$  V). Parameters that vary with supply voltage are illustrated in the *Typical Characteristics* section.

### 8.3.2 Rail-to-Rail Input

The input common-mode voltage range of the TLV600x series extends 200 mV beyond the supply rails. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the *Functional Block Diagram*. The N-channel pair is active for input voltages close to the positive rail, typically  $(V_+) - 1.3$  V to 200 mV above the positive supply, while the P-channel pair is on for inputs from 200 mV below the negative supply to approximately  $(V_+) - 1.3$  V. There is a small transition region, typically  $(V_+) - 1.4$  V to  $(V_+) - 1.2$  V, in which both pairs are on. This 200-mV transition region may vary up to 300 mV with process variation. Thus, the transition region (both stages on) may range from  $(V_+) - 1.7$  V to  $(V_+) - 1.5$  V on the low end, up to  $(V_+) - 1.1$  V to  $(V_+) - 0.9$  V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD may be degraded compared to device operation outside this region.

### 8.3.3 Rail-to-Rail Output

Designed as a micro-power, low-noise operational amplifier, the TLV600x delivers a robust output drive capability. A class AB output stage with common-source transistors is used to achieve full rail-to-rail output swing capability. For resistive loads up to 100 k $\Omega$ , the output swings typically to within 5 mV of either supply rail regardless of the power-supply voltage applied. Different load conditions change the ability of the amplifier to swing close to the rails, as shown in [Figure 11](#).

### 8.3.4 Common-Mode Rejection Ratio (CMRR)

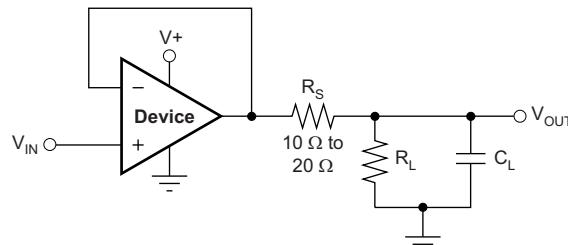
CMRR for the TLV600x is specified in several ways so the best match for a given application may be used; see *Electrical Characteristics*. First, the CMRR of the device in the common-mode range below the transition region [ $V_{CM} < (V_+) - 1.3$  V] is given. This specification is the best indicator of the capability of the device when the application requires the use of one of the differential input pairs. Second, the CMRR over the entire common-mode range is specified at ( $V_{CM} = -0.2$  V to 5.7 V). This last value includes the variations seen through the transition region, as shown in [Figure 4](#).

### 8.3.5 Capacitive Load and Stability

The TLV600x is designed to be used in applications where driving a capacitive load is required. As with all op amps, there may be specific instances where the TLV600x may become unstable. The particular op amp circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether or not an amplifier is stable in operation. An op amp in the unity-gain ( $1+V/V$ ) buffer configuration that drives a capacitive load exhibits a greater tendency to be unstable than an amplifier operated at a higher noise gain. The capacitive load, in conjunction with the op amp output resistance, creates a pole within the feedback loop that degrades the phase margin. The degradation of the phase margin increases as the capacitive loading increases. When operating in the unity-gain configuration, the TLV600x remains stable with a pure capacitive load up to approximately 1 nF. The equivalent series resistance (ESR) of some capacitors ( $C_L$  greater than 1  $\mu$ F) is sufficient to alter the phase characteristics in the feedback loop such that the amplifier remains stable. Increasing the amplifier closed-loop gain allows the amplifier to drive increasingly larger capacitance. This increased capability is evident when observing the overshoot response of the amplifier at higher voltage gains.

## Feature Description (continued)

One technique for increasing the capacitive load drive capability of the amplifier when it operates in a unity-gain configuration is to insert a small resistor, typically  $10\text{ }\Omega$  to  $20\text{ }\Omega$ , in series with the output, as shown in [Figure 19](#). This resistor significantly reduces the overshoot and ringing associated with large capacitive loads. One possible problem with this technique is that a voltage divider is created with the added series resistor and any resistor connected in parallel with the capacitive load. The voltage divider introduces a gain error at the output that reduces the output swing.



**Figure 19. Improving Capacitive Load Drive**

### 8.3.6 EMI Susceptibility and Input Filtering

Operational amplifiers vary with regard to the susceptibility of the device to electromagnetic interference (EMI). If conducted EMI enters the op amp, the dc offset observed at the amplifier output may shift from the nominal value while EMI is present. This shift is a result of signal rectification associated with the internal semiconductor junctions. While all op amp pin functions may be affected by EMI, the signal input pins are likely to be the most susceptible. The TLV600x family incorporates an internal input low-pass filter that reduces the amplifiers response to EMI. Common-mode and differential mode filtering are provided by this filter. The filter is designed for a cutoff frequency of approximately 35 MHz ( $-3\text{ dB}$ ), with a  $-20\text{ dB}$  per decade roll-off of 20 dB per decade.

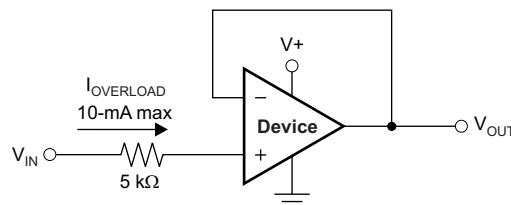
Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. The EMI rejection ratio (EMIRR) metric allows op amps to be directly compared by the EMI immunity. [Figure 18](#) illustrates the results of this testing on the TLV600x family. Detailed information may be found in [EMI Rejection Ratio of Operational Amplifiers](#) (SBOA128), available for download from [www.ti.com](http://www.ti.com).

## 8.4 Device Functional Modes

The TLV600x have a single functional mode. The devices are powered on as long as the power-supply voltage is between 1.8 V ( $\pm 0.9\text{ V}$ ) and 5.5 V ( $\pm 2.75\text{ V}$ ).

## 8.5 Input and ESD Protection

The TLV600x incorporates internal electrostatic discharge (ESD) protection circuits on all pins. In the case of input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. The ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA, as stated in the [Absolute Maximum Ratings](#) table. [Figure 20](#) shows how a series input resistor may be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.



**Figure 20. Input Current Protection**

## 9 Application and Implementation

### NOTE

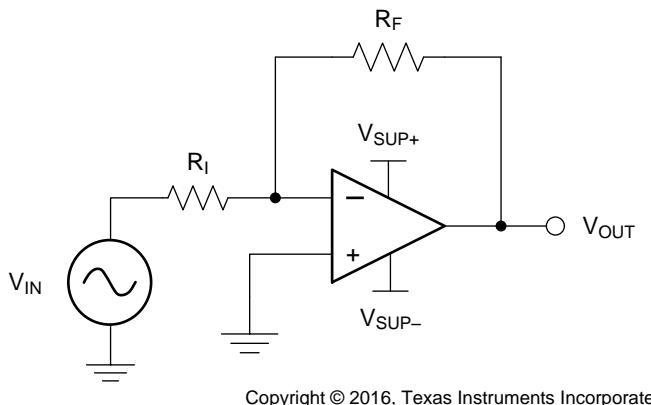
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The TLV600x is a family of low-power, rail-to-rail input and output operational amplifiers specifically designed for portable applications. The devices operate from 1.8 V to 5.5 V, are unity-gain stable, and are suitable for a wide range of general-purpose applications. The class AB output stage is capable of driving  $\leq 10\text{-k}\Omega$  loads connected to any point between  $V_+$  and ground. The input common-mode voltage range includes both rails, and allows the TLV600x to be used in any single-supply application.

### 9.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in [Figure 21](#). An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier makes negative input voltages positive on the output. In addition, amplification may be added by selecting the input resistor  $R_I$  and the feedback resistor  $R_F$ .



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**Figure 21. Application Schematic**

#### 9.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range ( $V_{CM}$ ) and the output voltage swing to the rails ( $V_O$ ) must be considered. For instance, this application scales a signal of  $\pm 0.5\text{ V}$  (1 V) to  $\pm 1.8\text{ V}$  (3.6 V). Setting the supply at  $\pm 2.5\text{ V}$  is sufficient to accommodate this application.

#### 9.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using [Equation 1](#) and [Equation 2](#):

$$A_V = \frac{V_{OUT}}{V_{IN}} = \frac{V_O}{V_{IN}} \quad (1)$$

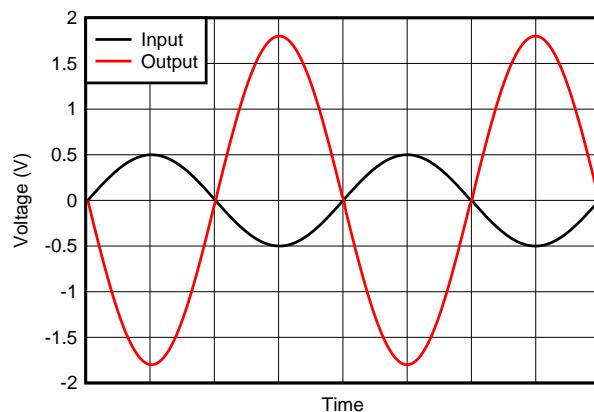
$$A_V = \frac{1.8}{-0.5} = -3.6 \quad (2)$$

## Typical Application (continued)

When the desired gain is determined, choose a value for  $R_I$  or  $R_F$ . Choosing a value in the kilohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures the device does not draw too much current. The trade-off is that large resistors (hundreds of kilohms) draw the smallest current but generate the highest noise. Small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k $\Omega$  for  $R_I$ , meaning 36 k $\Omega$  is used for  $R_F$ . The values are determined by [Equation 3](#):

$$A_V = -\frac{R_F}{R_I} \quad (3)$$

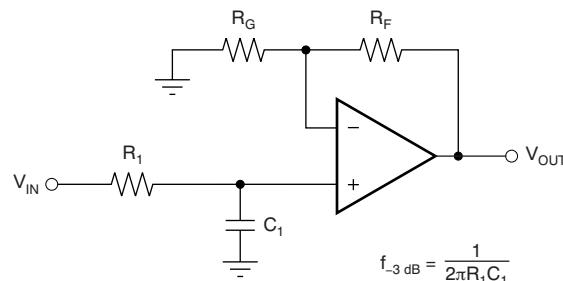
### 9.2.3 Application Curve



**Figure 22. Inverting Amplifier Input and Output**

## 9.3 System Examples

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to establish this limited bandwidth is to place an RC filter at the noninverting terminal of the amplifier, as shown in [Figure 23](#).

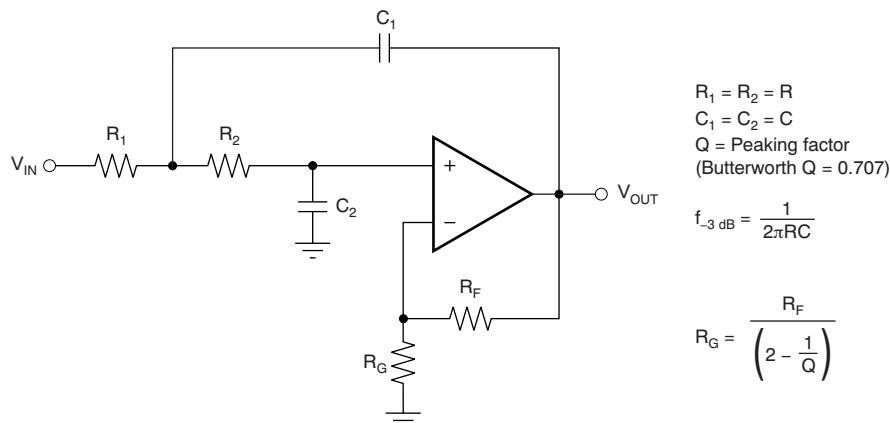


$$\frac{V_{\text{OUT}}}{V_{\text{IN}}} = \left(1 + \frac{R_F}{R_G}\right) \left( \frac{1}{1 + sR_1C_1} \right)$$

**Figure 23. Single-Pole Low-Pass Filter**

## System Examples (continued)

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter may be used for this task, as shown in [Figure 24](#). For best results, the amplifier must have a bandwidth that is eight to 10 times the filter frequency bandwidth. Failure to follow this guideline may result in phase shift of the amplifier.



**Figure 24. Two-Pole, Low-Pass, Sallen-Key Filter**

## 10 Power Supply Recommendations

The TLV600x is specified for operation from 1.8 V to 5.5 V ( $\pm 0.9$  V to  $\pm 2.75$  V); many specifications apply from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ . The [Typical Characteristics](#) presents parameters that may exhibit significant variance with regard to operating voltage or temperature.

**CAUTION**

Supply voltages larger than 7 V may permanently damage the device. (See the [Absolute Maximum Ratings](#) table).

Place 0.1- $\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see [Layout Guidelines](#).

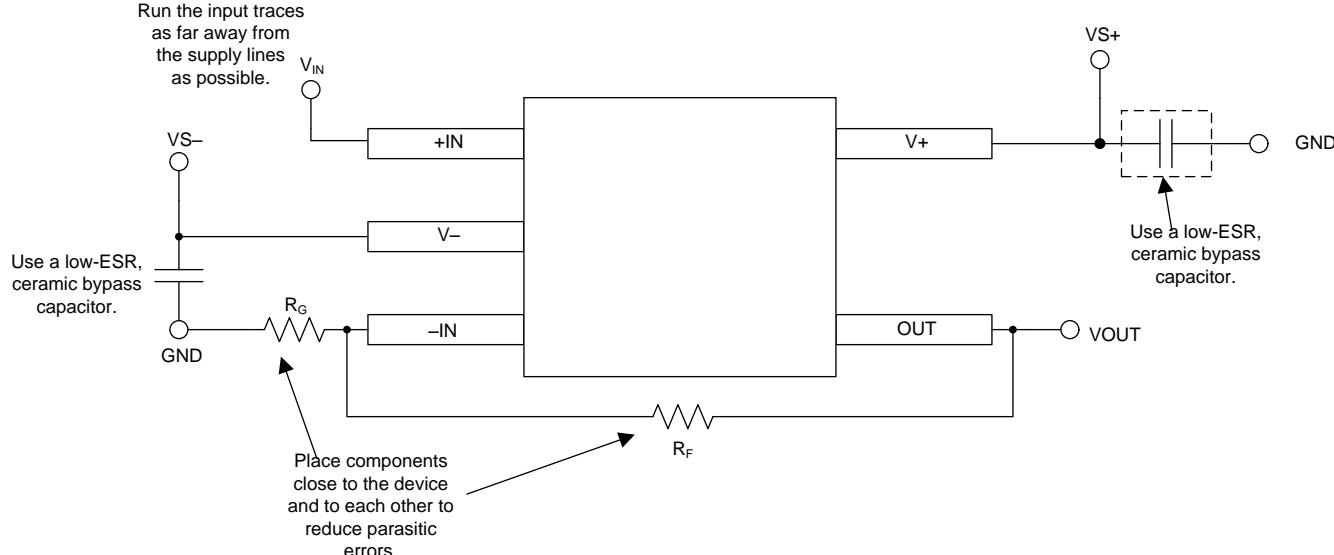
## 11 Layout

### 11.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

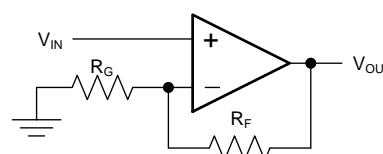
- Noise may propagate into analog circuitry through the power pins of the circuit and the operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1- $\mu$ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are typically devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, refer to *Circuit Board Layout Techniques* (SLOA089).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If the traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep  $R_F$  and  $R_G$  close to the inverting input in order to minimize parasitic capacitance, as shown in Figure 25.
- Keep the length of input traces as short as possible. Remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring may significantly reduce leakage currents from nearby traces that are at different potentials.

### 11.2 Layout Example



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**Figure 25. Operational Amplifier Board Layout for Noninverting Configuration**



**Figure 26. Schematic Representation of Figure 25**

## 12 Device and Documentation Support

### 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation, see the following:

- [EMI Rejection Ratio of Operational Amplifiers](#) (SBOA128)
- [Circuit Board Layout Techniques](#) (SLOA089)

### 12.2 Related Links

**Table 2** lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

**Table 2. Related Links**

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TLV6001	<a href="#">Click here</a>				
TLV6002	<a href="#">Click here</a>				
TLV6004	<a href="#">Click here</a>				

### 12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 12.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** **TI's Engineer-to-Engineer (E2E) Community.** Created to foster collaboration among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** **TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 12.5 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

### 12.6 Electrostatic Discharge Caution

 This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

 ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 12.7 Glossary

[SLYZ022 — TI Glossary](#).

This glossary lists and explains terms, acronyms, and definitions.

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV6001IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	Call TI   SN   NIPDAU	Level-2-260C-1 YEAR	-40 to 125	14W2	Samples
TLV6001IDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	Call TI   SN   NIPDAU	Level-2-260C-1 YEAR	-40 to 125	14W2	Samples
TLV6001IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 125	13X	Samples
TLV6001IDCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 125	13X	Samples
TLV6001RIDBVR	NRND	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1602	
TLV6001RIDBVT	NRND	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	1602	
TLV6001UIDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	16P2	Samples
TLV6001UIDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	16P2	Samples
TLV6002IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG   SN	Level-2-260C-1 YEAR	-40 to 125	14TV	Samples
TLV6002IDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAUAG   SN	Level-2-260C-1 YEAR	-40 to 125	14TV	Samples
TLV6002IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 125	(TL6002, V6002)	Samples
TLV6004IPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU   SN	Level-2-260C-1 YEAR	-40 to 125	TLV6004	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBsolete:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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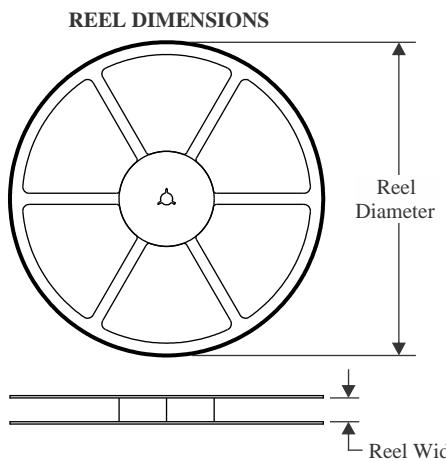
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF TLV6001, TLV6002 :**

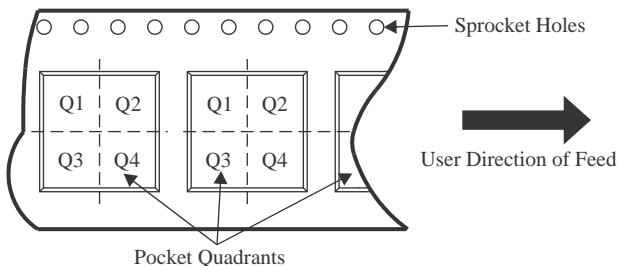
- Automotive : [TLV6001-Q1](#), [TLV6002-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

**TAPE AND REEL INFORMATION**


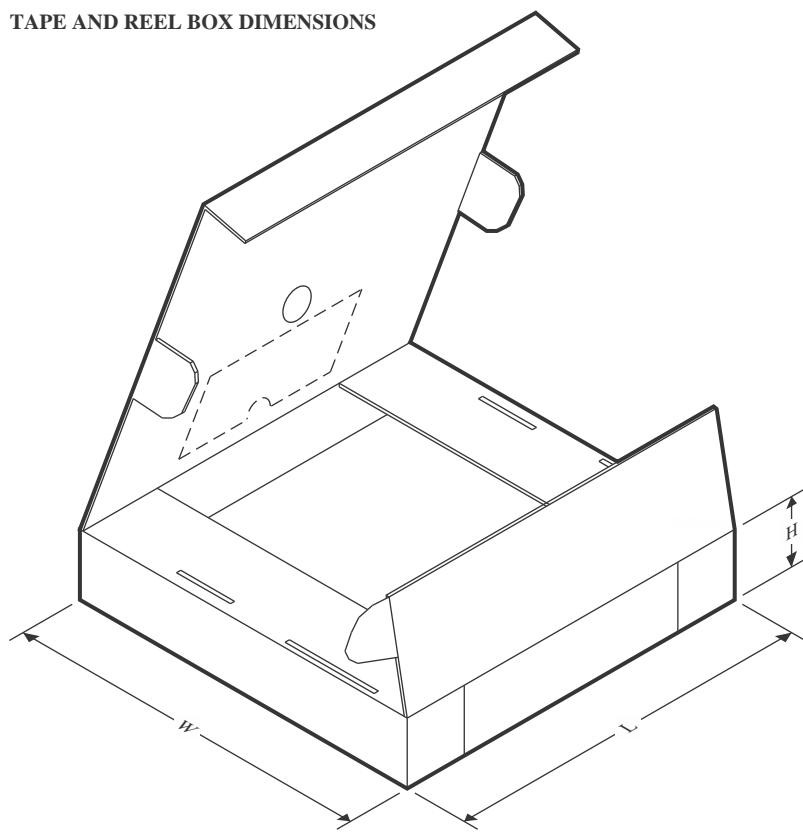
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV6001IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001IDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001IDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV6001IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV6001IDCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV6001IDCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
TLV6001RIDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV6001RIDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV6001UIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001UIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001UIDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6001UIDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV6002IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV6002IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV6002IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV6002IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV6002IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV6004IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLV6004IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV6001IDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV6001IDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV6001IDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV6001IDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV6001IDCKR	SC70	DCK	5	3000	190.0	190.0	30.0
TLV6001IDCKR	SC70	DCK	5	3000	180.0	180.0	18.0
TLV6001IDCKT	SC70	DCK	5	250	190.0	190.0	30.0
TLV6001IDCKT	SC70	DCK	5	250	180.0	180.0	18.0
TLV6001RIDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV6001RIDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV6001UIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV6001UIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV6001UIDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV6001UIDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV6002IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
TLV6002IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
TLV6002IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
TLV6002IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0

---

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV6002IDR	SOIC	D	8	2500	340.5	336.1	25.0
TLV6004IPWR	TSSOP	PW	14	2000	366.0	364.0	50.0
TLV6004IPWR	TSSOP	PW	14	2000	356.0	356.0	35.0

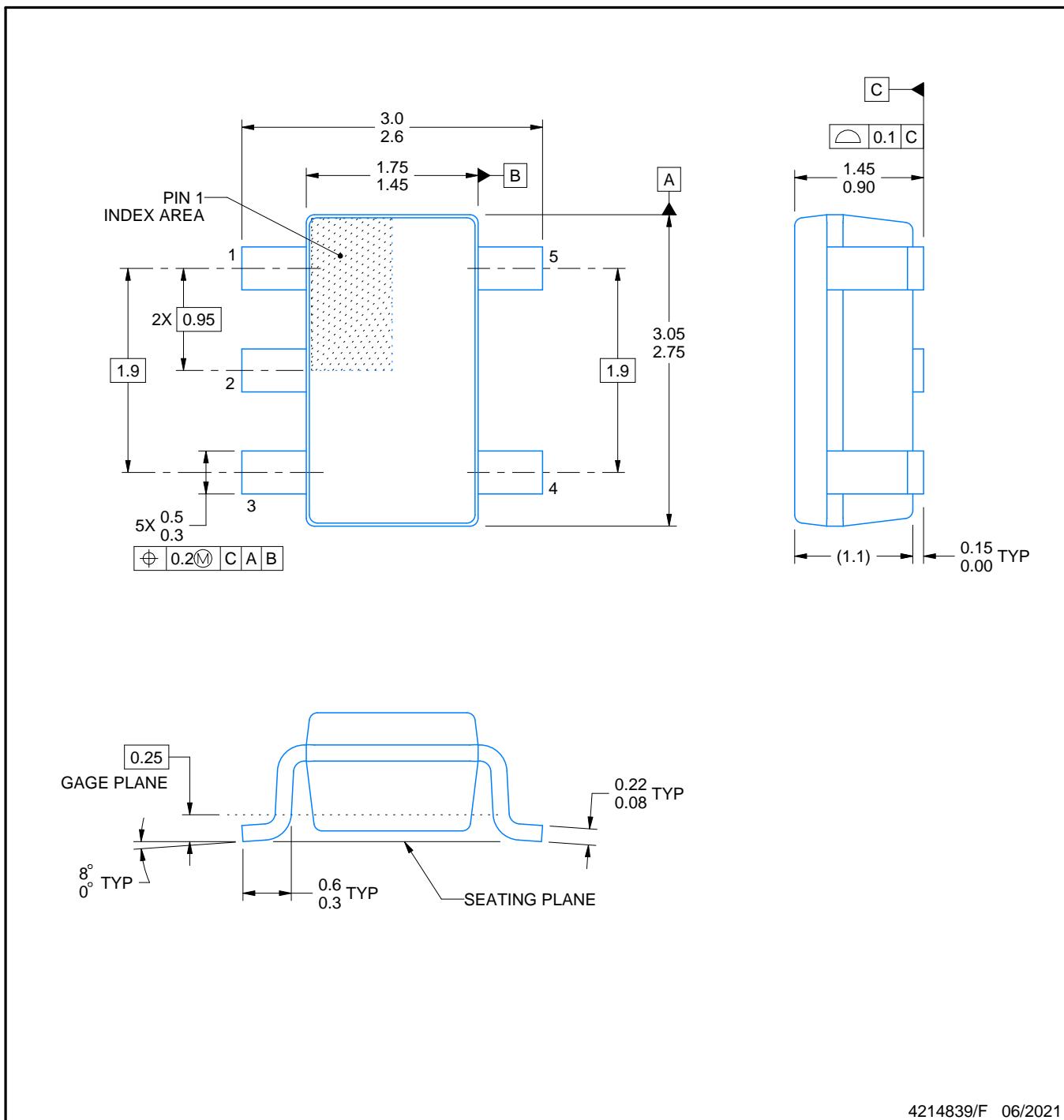
# PACKAGE OUTLINE

DBV0005A



SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



## NOTES:

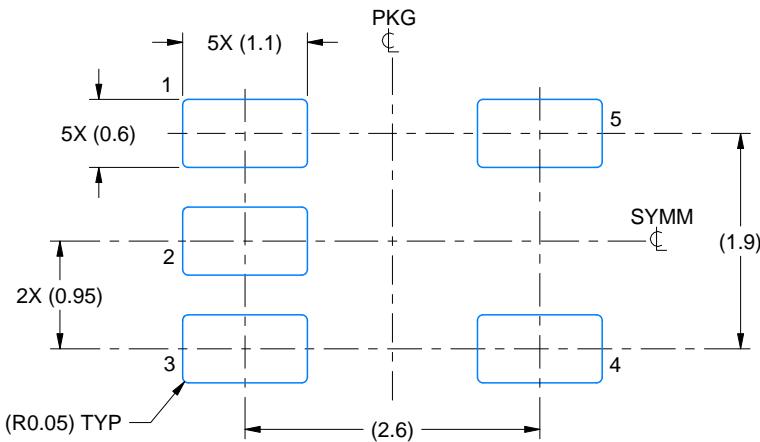
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

# EXAMPLE BOARD LAYOUT

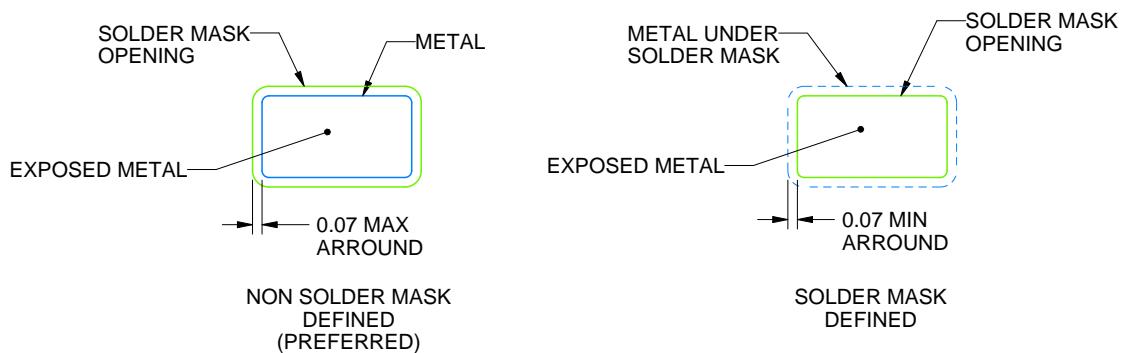
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214839/F 06/2021

NOTES: (continued)

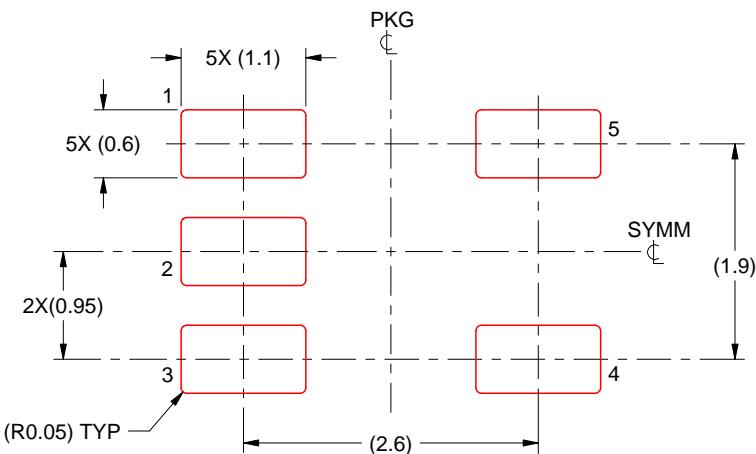
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

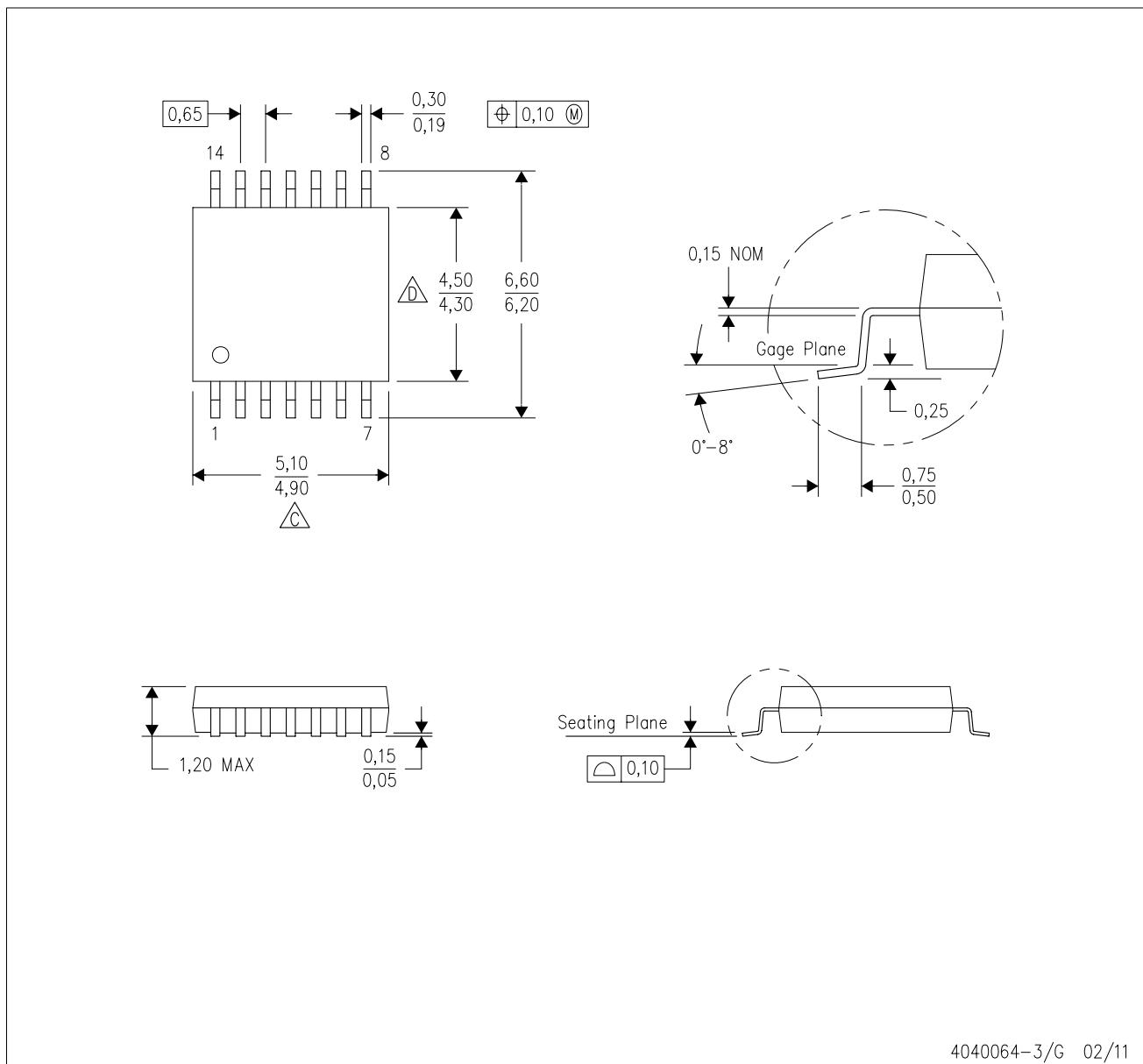
4214839/F 06/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



4040064-3/G 02/11

NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

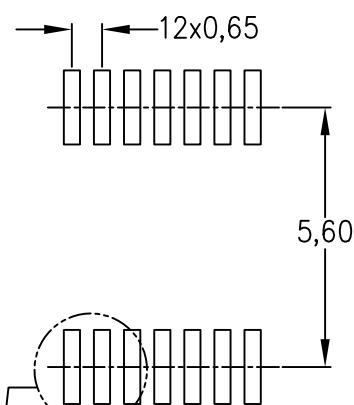
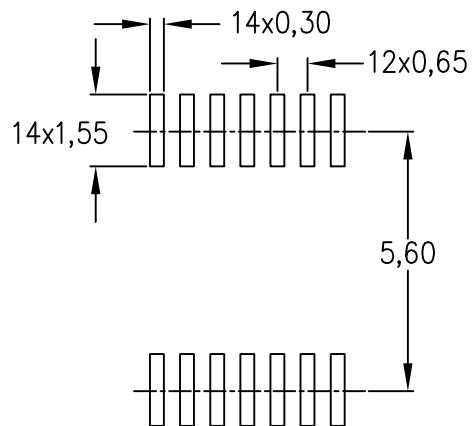
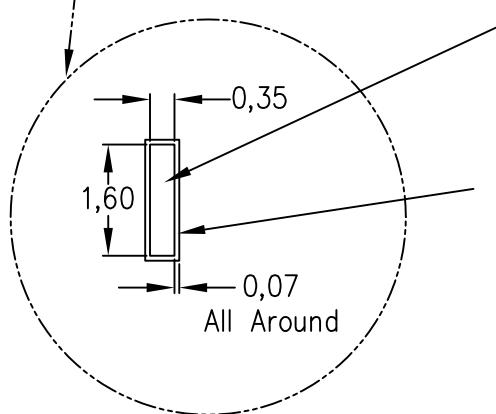
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO-153

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE

Example Board Layout  
(Note C)Stencil Openings  
(Note D)Example  
Non Soldermask Defined PadExample  
Pad Geometry  
(See Note C)Example  
Solder Mask Opening  
(See Note E)

4211284-2/G 08/15

## NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

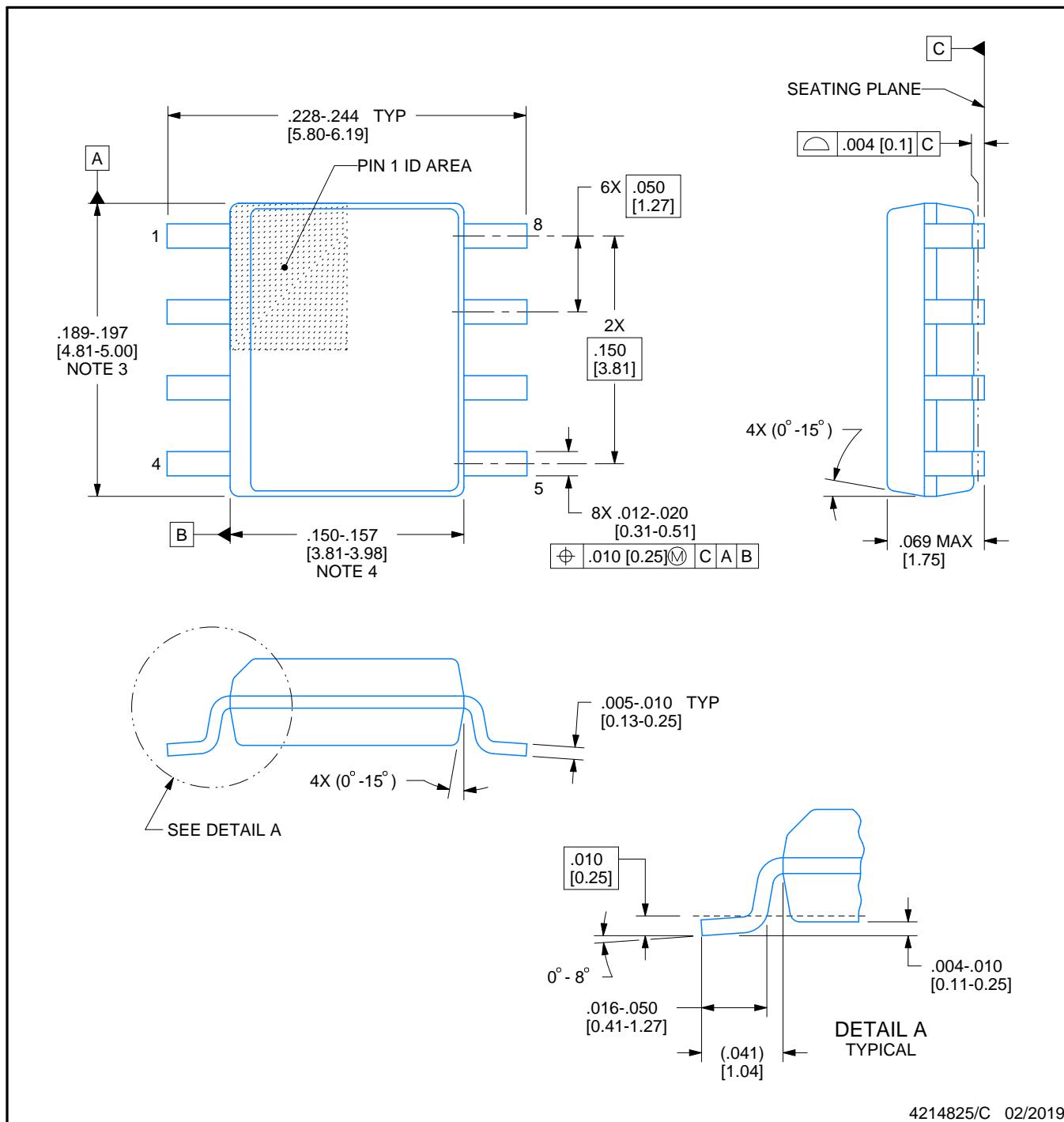


## PACKAGE OUTLINE

**D0008A**

## SOIC - 1.75 mm max height

## SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

## NOTES:

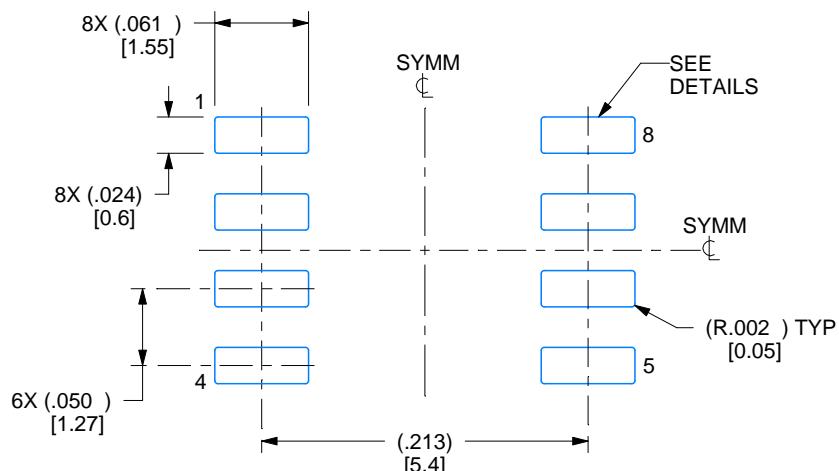
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

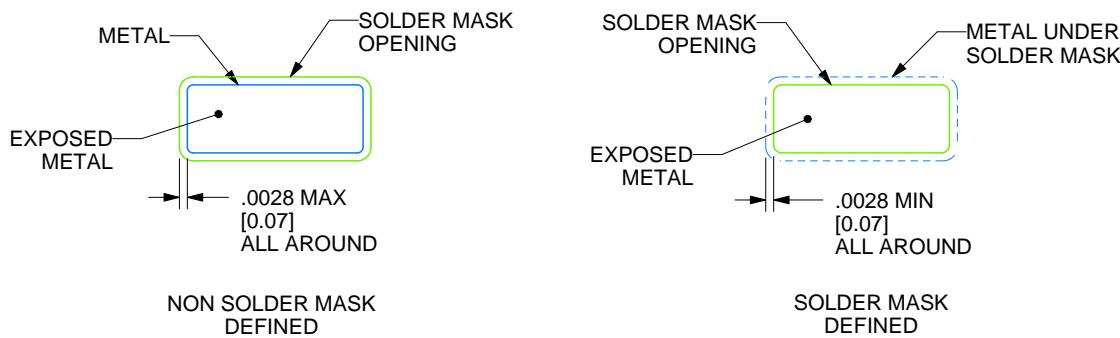
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

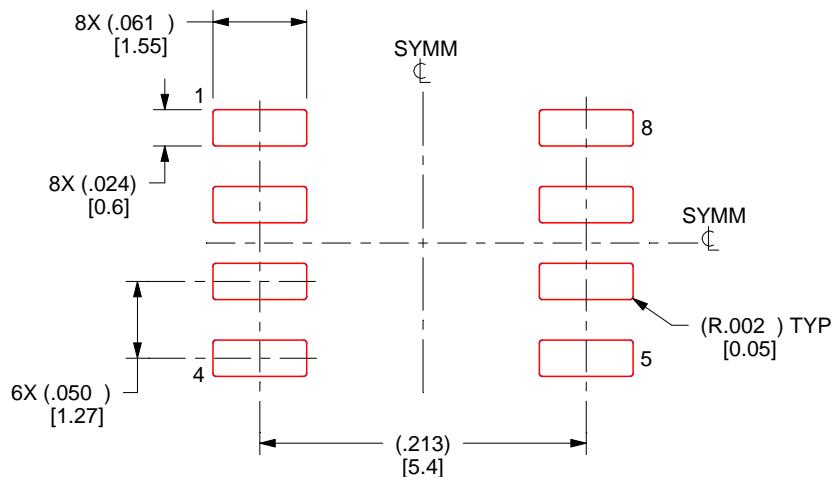
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

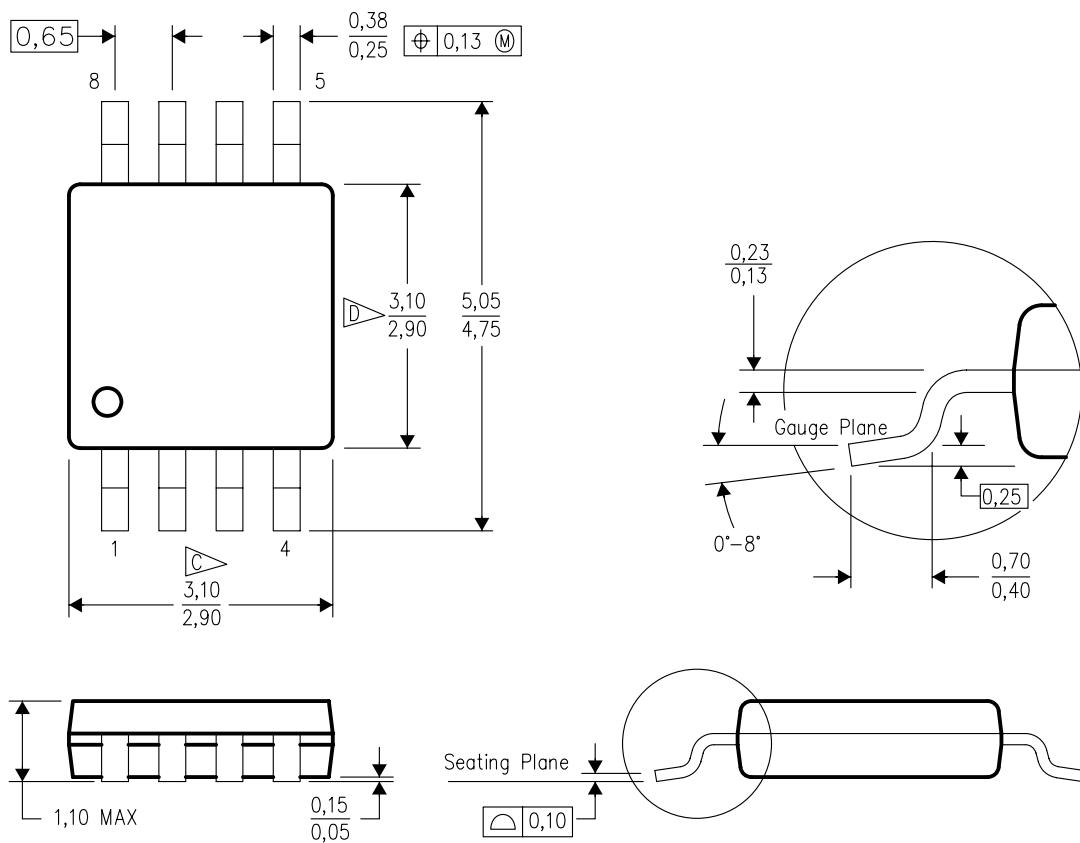
4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## DGK (S-PDSO-G8)

## PLASTIC SMALL-OUTLINE PACKAGE



4073329/E 05/06

NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

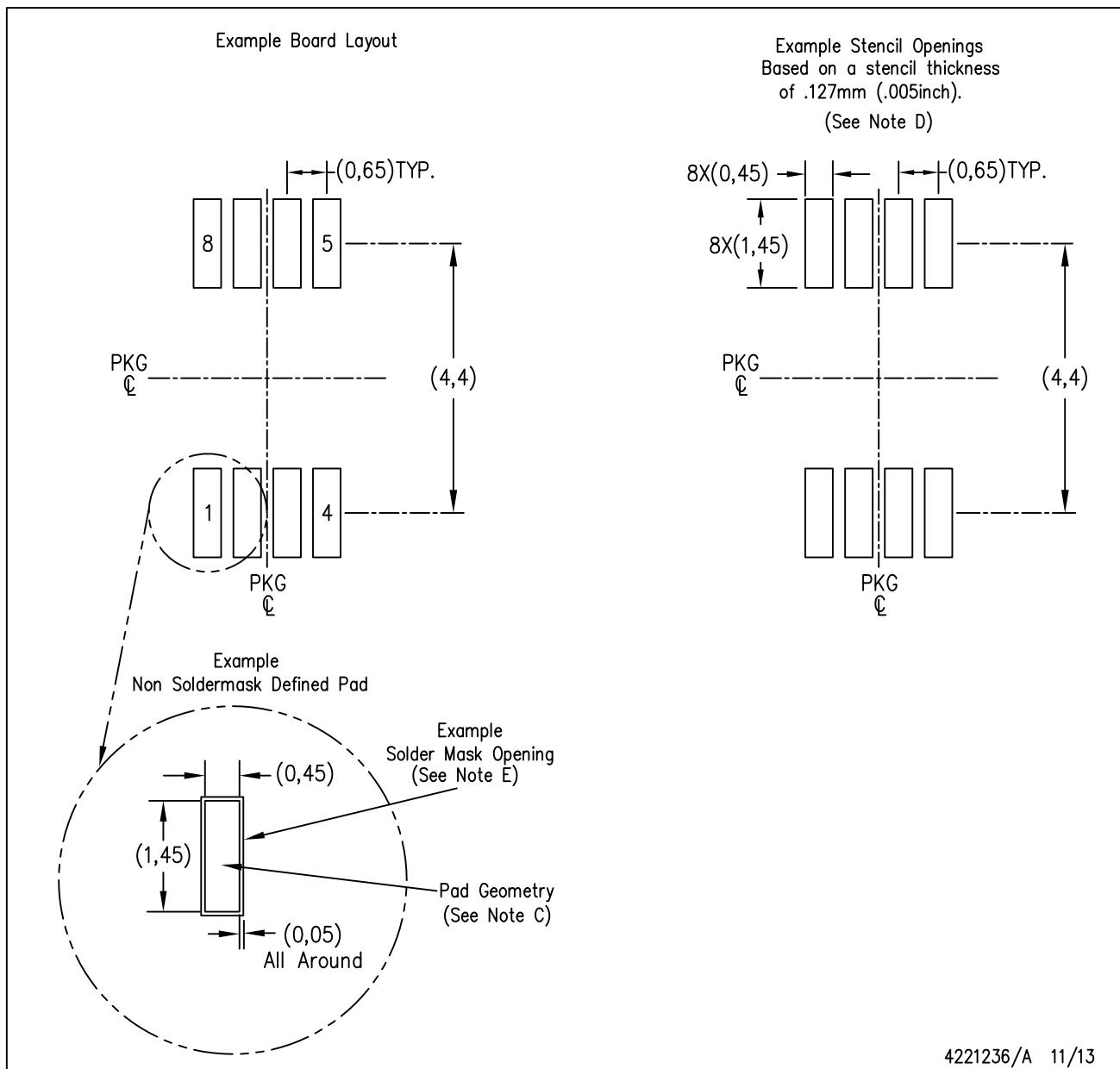
 C Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.

 D Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.

E. Falls within JEDEC MO-187 variation AA, except interlead flash.

DGK (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE

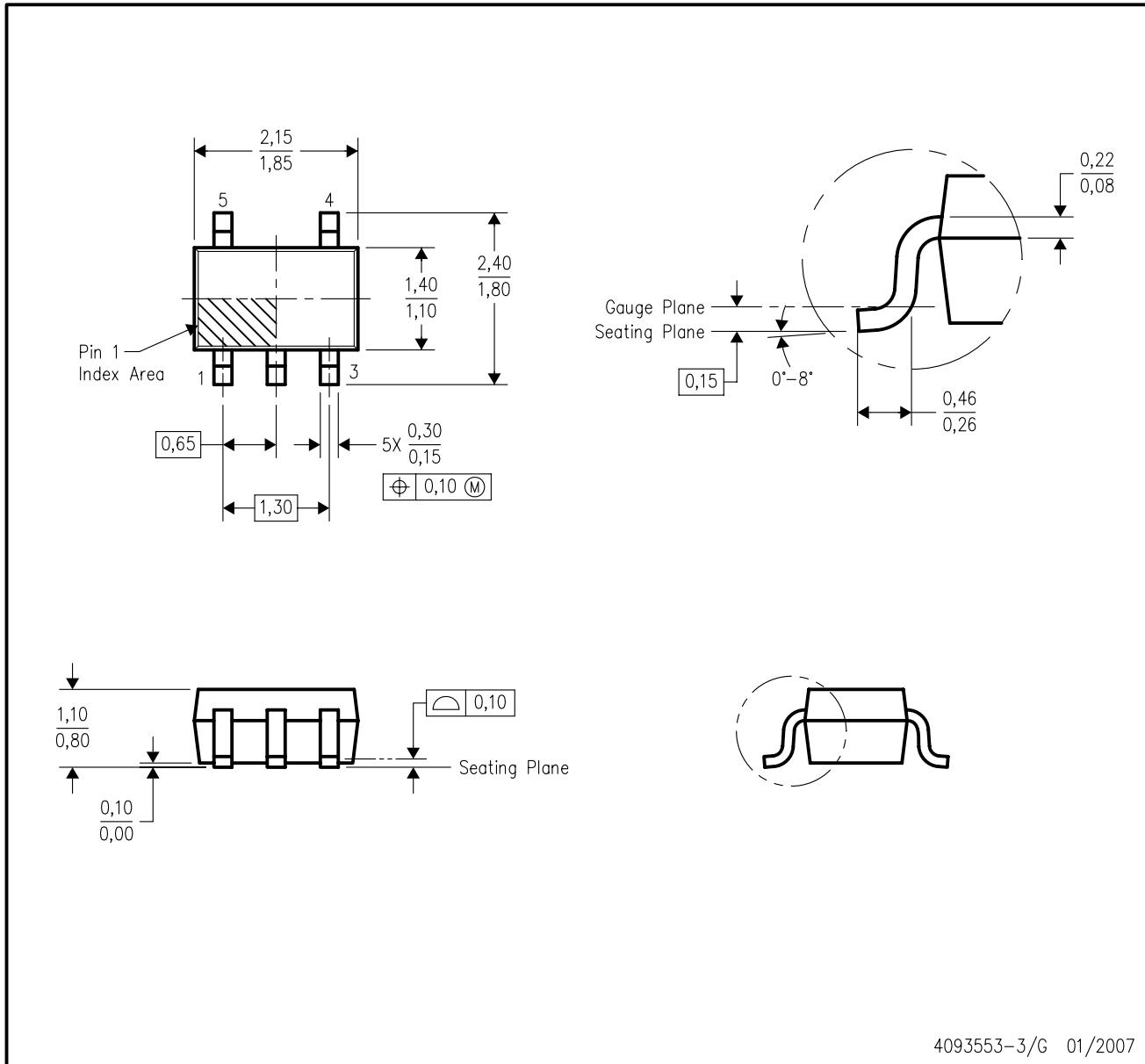


NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Publication IPC-7351 is recommended for alternate designs.
- Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

## DCK (R-PDSO-G5)

## PLASTIC SMALL-OUTLINE PACKAGE



4093553-3/G 01/2007

NOTES:

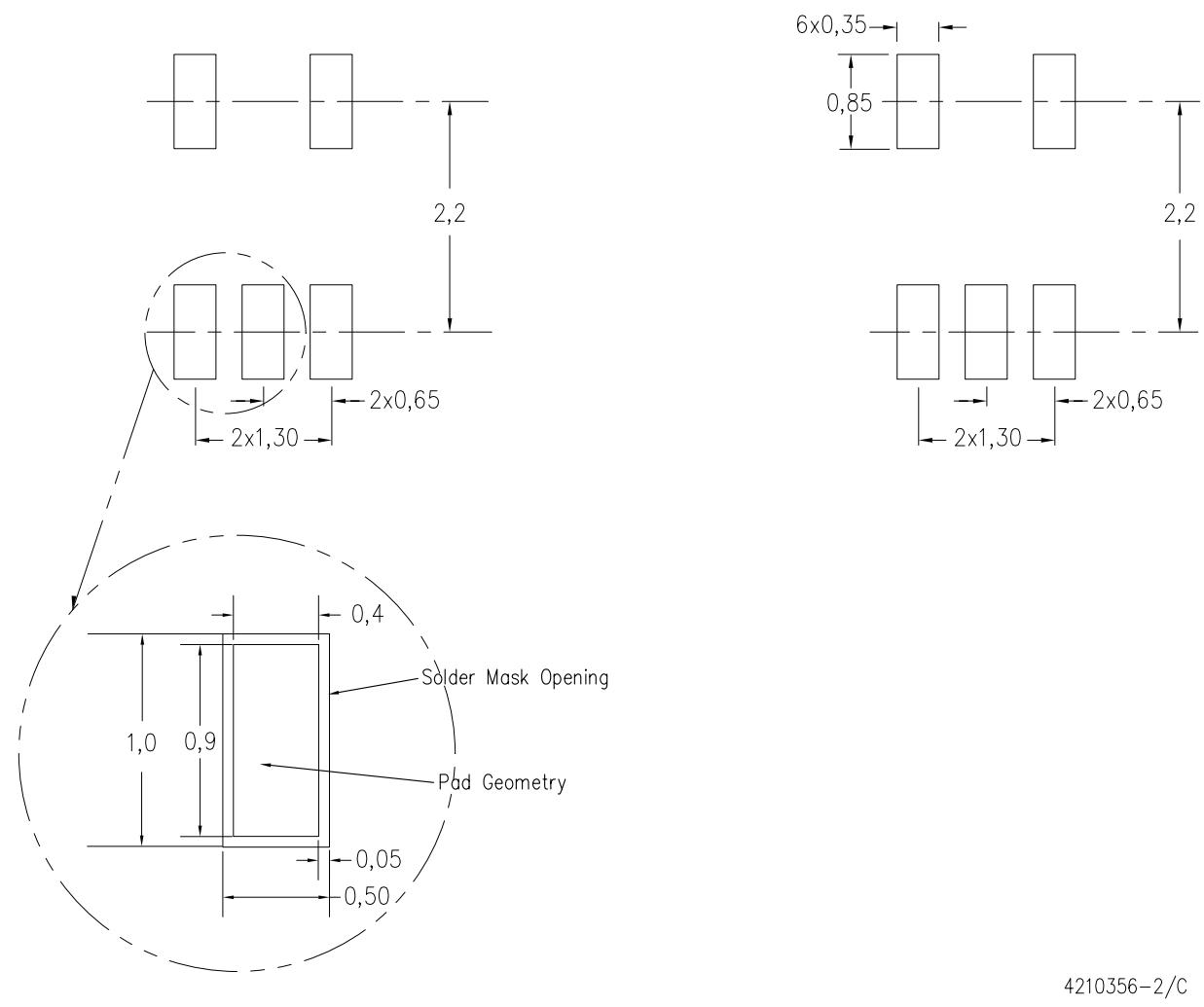
- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE

Example Board Layout

Stencil Openings  
Based on a stencil thickness  
of .127mm (.005inch).



NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- Publication IPC-7351 is recommended for alternate designs.
- Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.

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